



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 10V$	380mA
000	3Ω @ $V_{GS} = 5V$	310mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

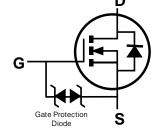
Mechanical Data

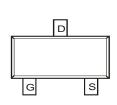
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)





SOT323





Top View

Equivalent Circuit

Top View

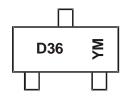
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D1LW-7	SOT323	3000/Tape & Reel
DMN63D1LW-13	SOT323	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D36 = Product Type Marking Code $YM = Date Code Marking Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)$

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н	ı	J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit			
Drain-Source Voltage		V _{DSS}	60	V		
Gate-Source Voltage		V _{GSS}	±20	V		
Continuous Prain Correct (Note C) // 40//	Steady State	T _A = +25°C T _A = +70°C	I _D	380 300	mA	
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	430 340	mA			
Maximum Continuous Body Diode Forward Current	(Note 6)	Is	0.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	b) (Note 6)		I _{DM}	1.2	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	310	mW	
Thermal Decistones, Junction to Ambient (Note E)	Steady State	В	411	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	371	C/VV
Total Power Dissipation (Note 6)		P _D	410	mW
Thermal Decistores, Junction to Ambient (Note C)	Steady State	311		°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	257	C/VV
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

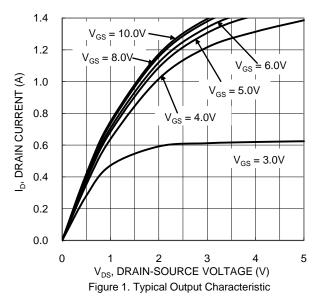
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

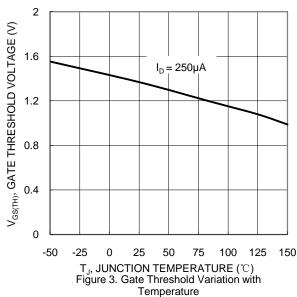
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	•					
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	V _{DS} = 10V, I _D = 1mA
Static Drain-Source On-Resistance	0		_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Dialit-Source Off-Resistance	R _{DS(ON)}		_	3.0	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}	_	0.75	1.1	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	30	_	pF	
Output Capacitance	Coss	_	4.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	2.9	_	pF	1 – 1.00012
Gate Resistance	Rg	_	133	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	_	304	_	рС	
Gate-Source Charge	Q _{gs}	_	203	_	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250 \text{mA}$
Gate-Drain Charge	Q _{gd}	_	84	_	рC	1D - 20011A
Turn-On Delay Time	t _{D(ON)}	_	3.9	_	ns	
Turn-On Rise Time	t _R	_	3.4	_	ns	V _{DD} = 30V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}	_	15.7	_	ns	$R_G = 25\Omega$, $I_D = 200 \text{mA}$
Turn-Off Fall Time	t _F	_	9.9	_	ns	

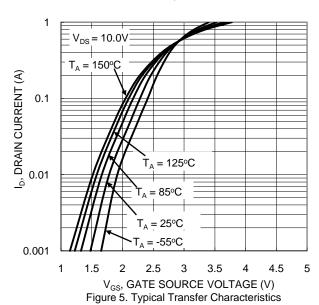
Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.









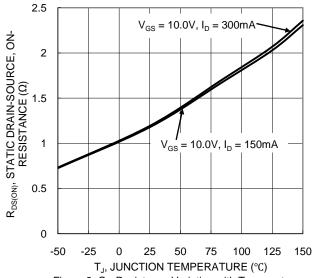
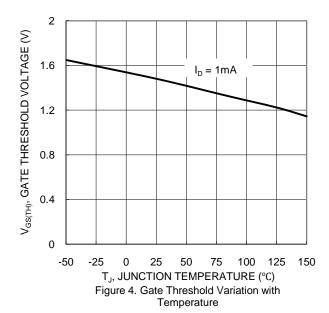


Figure 2. On-Resistance Variation with Temperature

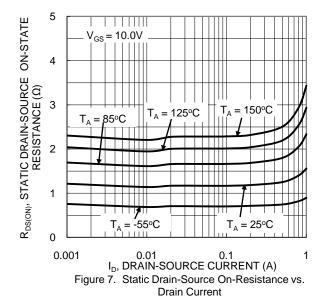


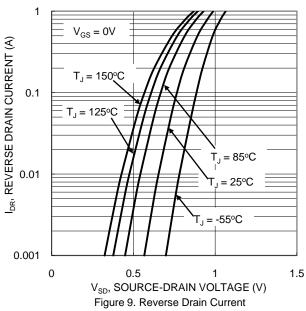
T_A = 85°C T_A = 125°C T_A = 150°C T_A = 25°C T_A

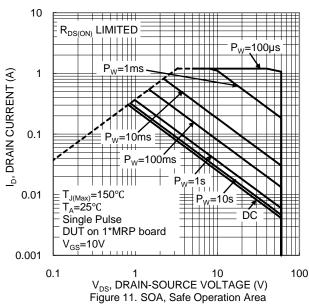
Figure 6. Static Drain-Source On-Resistance vs.

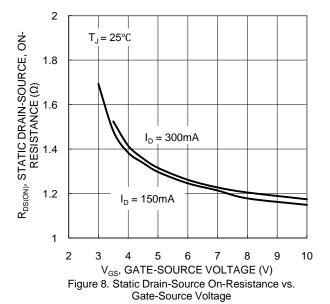
Drain Current

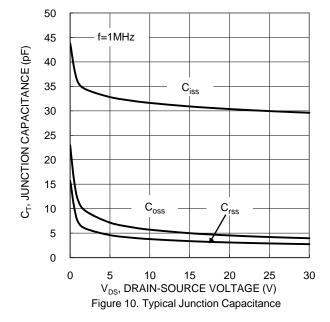




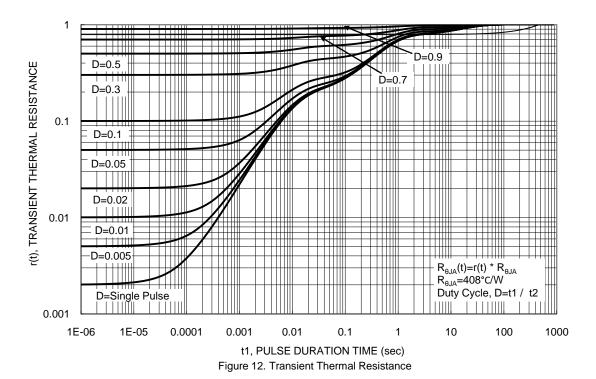






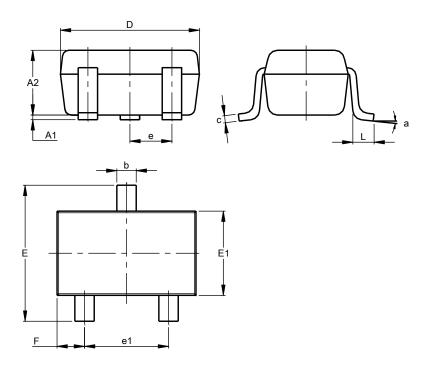






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

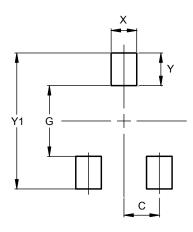


SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	0.650 BSC							
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	a 8°							
All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	1.300 0.470		
Х			
Y	0.600		
Y1	2.500		

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